

ABSTRACT

A reflective mask blank is a material for a reflective mask used in EUV lithography using EUV light as exposure light. The reflective mask blank comprising: a substrate (1); a multilayer reflective film (2) that reflects the exposure light and is formed above one main surface of the substrate (1); a protective film (3) that protects the multilayer reflective film (2) and is formed above the multilayer reflective film (2); an absorption film (5) that absorbs the exposure light and is formed above the protective film (3); and an etch-stop film (4) that contains niobium (Nb) and is provided between the protective film (3) and the absorption film (5). The protective film (3) has at least one layer containing rhodium (Rh). A layer in contact with the protective film (3) in the multilayer reflective film (2) contains molybdenum (Mo).

Fig. 1